

Features

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Positive Temperature Coefficient on V_F

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters





Part Number	Package	Qty(PCS)		
HNDSH20120CDN	TO247-3L	30		

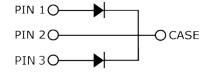
Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V _{RSM}	Surge Peak Reverse Voltage	1300	V		
V _{DC}	DC Blocking Voltage	1200	V		
I _F	Continuous Forward Current (Per Leg/Device)	34/68 16.5/33 10/20	А	T _c =25°C T _c =135°C T _c =157°C	Fig. 3
I _{FRM}	Repetitive Peak Forward Surge Current	47* 31.5*	Α	T_c =25°C, t_p =10 ms, Half Sine Pulse T_c -110°C, t_p =10 ms, Half Sine Pulse	
I _{FSM}	Non-Repetitive Peak Forward Surge Current	71* 59.5*	А	T _c =25°C, t _p =10 ms, Half Sine Pulse T _c =110°C, t _p =10 ms, Half Sine Pulse	Fig. 8
I _{F,Max}	Non-Repetitive Peak Forward Current	750* 620*	Α	T_c =25°C, t_p =10 ms, Pulse T_c =110°C, t_p =10 ms, Pulse	Fig. 8
P _{tot}	Power Dissipation(Per Leg/Device)	176/352 76/152	W	T _c =25°C T _c =110°C	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	V _R =0-960V	
∫i²dt	i²t value	25* 17.5*	A ² s	T _C =25°C, t _p =10 ms T _C =110°C, t _p =10 ms	
T _J	Operating Junction Range	-55 to +175	°C		
T _{stg}	Storage Temperature Range	-55 to +135	°C		
	TO-247 Mounting Torque	1	Nm Ibf in	M3 Screw	

^{*} Per Leg, ** Per Device







Electrical Characteristics (Per Leg)

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V _F	Forward Voltage	1.5 2.2	1.8 3	V	I _F = 10 A T _J =25°C I _F = 10 A T _J =175°C	Fig. 1
I _R	Reverse Current	30 55	250 350	μΑ	V _R = 1200 V T _J =25°C V _R = 1200 V T _J =175°C	Fig. 2
Q _c	Total Capacitive Charge	52		nC	$V_R = 800 \text{ V, } I_F = 10\text{A}$ $di/dt = 200 \text{ A/}\mu\text{s}$ $T_J = 25^{\circ}\text{C}$	Fig. 5
С	Total Capacitance	754 45 38		pF	V _R = 0 V, T _J = 25°C, f = 1 MHz V _R = 400 V, T _J = 25°C, f = 1 MHz V _R = 800 V, T _J = 25°C, f = 1 MHz	Fig. 6
E _c	Capacitance Stored Energy	14.5		μJ	V _R = 800 V	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Тур.	Unit	Note
R _{eJC}	Thermal Resistance from Junction to Case	0.85* 0.43**	°C/W	Fig. 9

^{*} Per Leg, ** Per Device

Typical Performance (Per Leg)

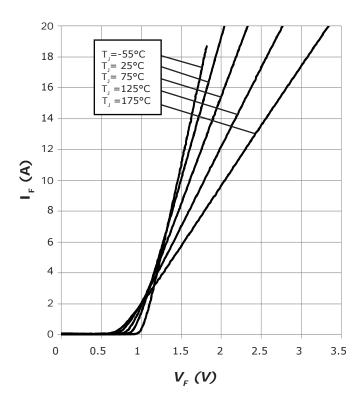


Figure 1. Forward Characteristics

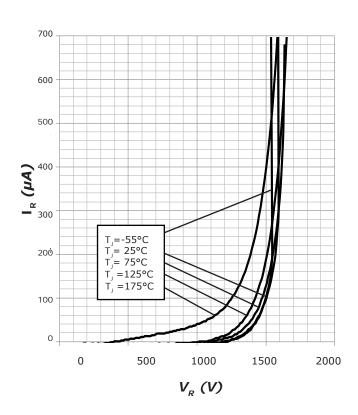


Figure 2. Reverse Characteristics



Typical Performance (Per Leg)

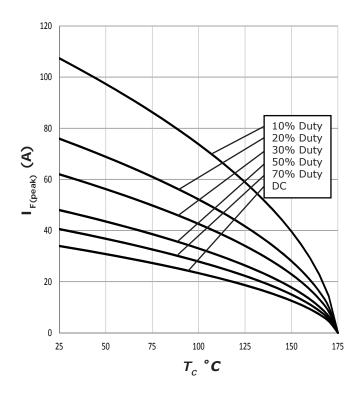


Figure 3. Current Derating

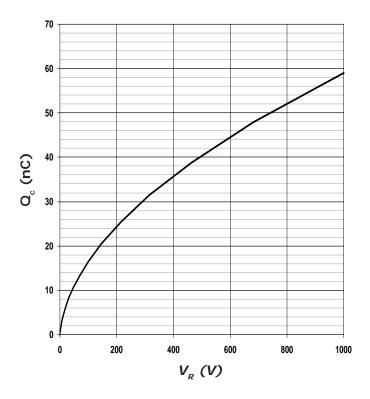


Figure 5. Recovery Charge vs. Reverse Voltage

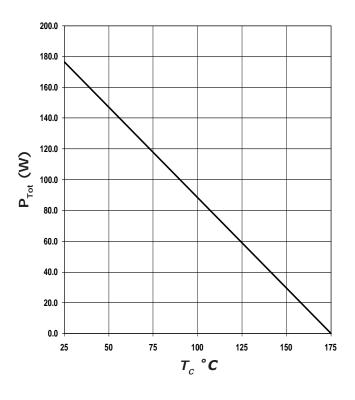


Figure 4. Power Derating

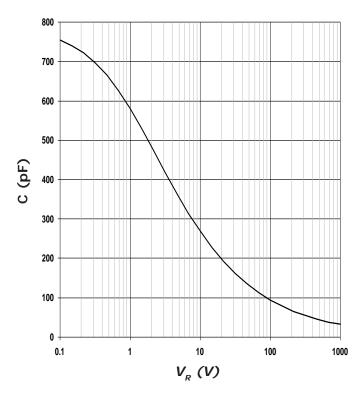


Figure 6. Capacitance vs. Reverse Voltage

Silicon Carbide Schottky Diode

Typical Performance

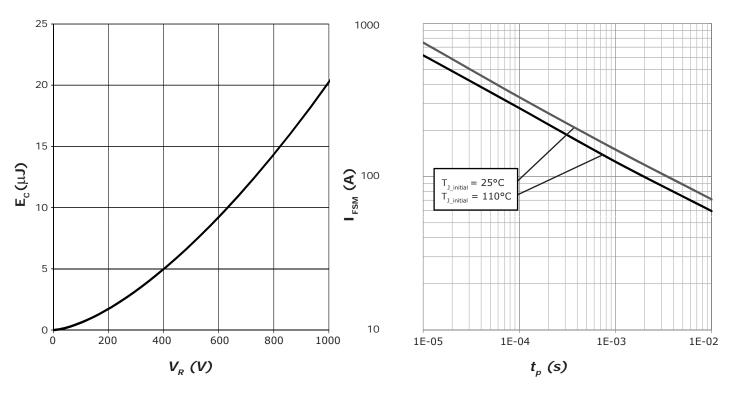


Figure 7. Typical Capacitance Stored Energy, per leg

Figure 8. Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform), per leg

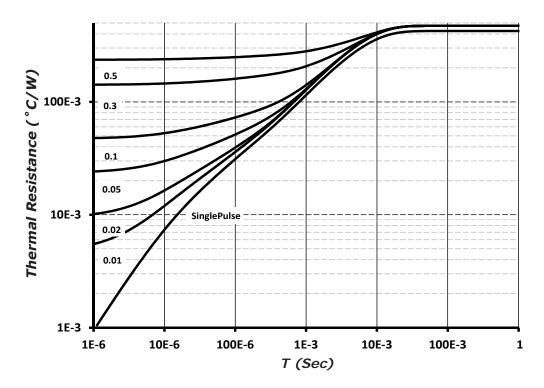


Figure 9. Device Transient Thermal Impedance

Diode Model

$$\begin{array}{c|c} - & & \\ \hline V_T & R_T \end{array}$$

$$V_{fT} = V_T + If * R_T$$

$$V_T = 0.98 + (T_J^* - 1.71^*10^{-3})$$

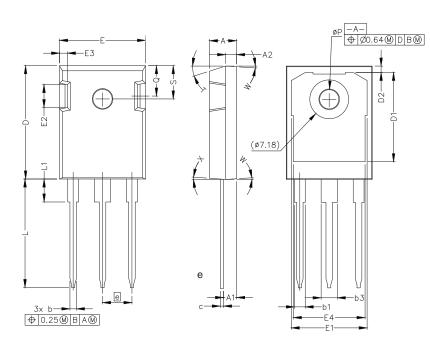
 $R_T = 0.040 + (T_J^* 5.32^*10^{-4})$

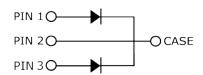
Note: T_j = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C



Package Dimensions

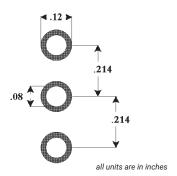
Package TO247-3L





POS	Inc	hes	Millimeters		
	Min	Max	Min	Max	
А	.190	.205	4.83	5.21	
A1	.090	.100	2.29	2.54	
A2	.075	.085	1.91	2.16	
b	.042	.052	1.07	1.33	
b1	.075	.095	1.91	2.41	
b3	.113	.133	2.87	3.38	
С	.022	.027	0.55	0.68	
D	.819	.831	20.80	21.10	
D1	.640	.695	16.25	17.65	
D2	.037	.049	0.95	1.25	
Е	.620	.635	15.75	16.13	
E1	.516	.557	13.10	14.15	
E2	.145	.201	3.68	5.10	
E3	.039	.075	1.00	1.90	
E4	.487	.529	12.38	13.43	
е	.214	BSC	5.44 BSC		
L	.780	.800	19.81	20.32	
L1	.161	.173	4.10	4.40	
N	3				
ØP	.138	.144	3.51	3.65	
Q	.216	.236	5.49	6.00	
S	.238	.248	6.04	6.30	
Т	17.5° REF				
W	3.5° REF				
Х	4° REF				

Recommended Solder Pad Layout



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